

**Product data sheet** 

# 1. General description

Dual ultrafast power diode in a SOT429 (3-lead TO-247) plastic package.

## 2. Features and benefits

- Very low on-state loss
- Fast switching
- Low leakage current
- Low thermal resistance

# 3. Applications

- Active PFC in air conditioner
- Interleaved PFC topology in switched-mode power supplies

## 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>R</sub>	reverse voltage	DC	-	-	600	V
I <sub>F(AV)</sub>	average forward current	δ = 0.5 ; T <sub>mb</sub> ≤ 127 °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	-	15	A
I <sub>FRM</sub>	repetitive peak forward current	δ = 0.5 ; t <sub>p</sub> = 25 μs; T <sub>mb</sub> ≤ 127 °C; Square-ware pulse	-	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	$t_p$ = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	-	150	A
		$t_p$ = 8.3 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode; Fig. 4	-	-	165	A
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.4	2.1	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.1	1.8	V
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	25	50	ns
		$I_F$ = 15 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/ µs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	45	-	ns
		I <sub>F</sub> = 15 A; V <sub>R</sub> = 400 V; dI <sub>F</sub> /dt = 200 A/ μs; T <sub>j</sub> = 125 °C; <u>Fig. 7</u>	-	65	-	ns

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# BYV415W-600P

### Dual ultrafast power diode

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$I_F = 15 \text{ A};  V_R = 400 \text{ V};  dI_F/\text{d}t = 500 \text{ A}/ \\ \mu \text{s};  T_j = 25 ^\circ\text{C};  \underline{\text{Fig. } 7}$	-	34	-	ns

## 5. Pinning information

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Table 2.	Pinning in	formation		
Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode 1		
2	К	cathode		
3	A2	anode 2		K sym125
mb	mb	mounting base; connected to cathode		
			TO-247 (SOT429)	

# 6. Ordering information

Table 3. Ordering inform	mation				
Type number	Package				
	Name	Description	Version		
BYV415W-600P	TO-247	plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3 lead TO-247	SOT429		

#### BYV415W-600P



## 7. Limiting values

### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>RRM</sub>	repetitive peak reverse voltage		-	600	V
V <sub>RWM</sub>	crest working reverse voltage		-	600	V
V <sub>R</sub>	reverse voltage	DC	-	600	V
I <sub>F(AV)</sub>	average forward current	$\delta = 0.5$ ; $T_{mb} \le 127$ °C; square-wave pulse; Fig. 1; Fig. 2; Fig. 3	-	15	A
I <sub>O(AV)</sub>	average output current	$\delta = 0.5$ ; T <sub>mb</sub> $\leq$ 117 °C; square-wave pulse; both diodes conducting	-	30	A
I <sub>FRM</sub>	repetitive peak forward current	$\delta$ = 0.5 ; t <sub>p</sub> = 25 µs; T <sub>mb</sub> ≤ 127 °C; Square-ware pulse	-	30	A
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 10 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	-	150	A
		t <sub>p</sub> = 8.3 ms; T <sub>j(init)</sub> = 25 °C; sine-wave pulse; per diode; <u>Fig. 4</u>	-	165	A
T <sub>stg</sub>	storage temperature		-65	175	°C
Tj	junction temperature		-	175	°C

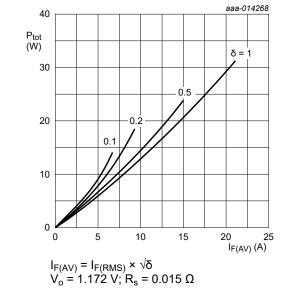
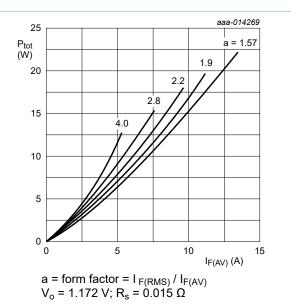


Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values

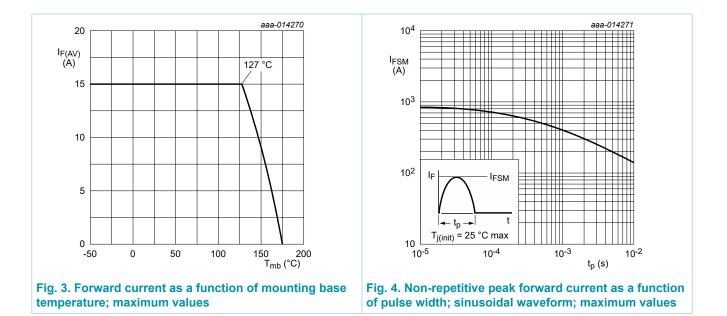




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### **Dual ultrafast power diode**



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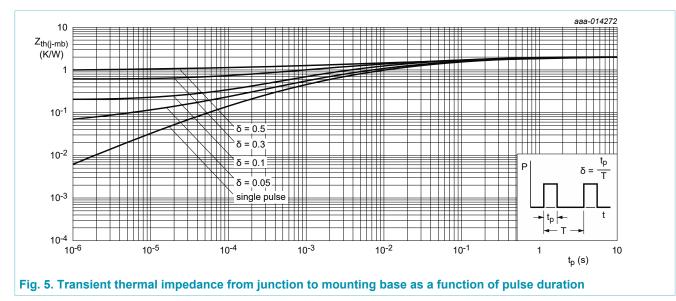
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**Dual ultrafast power diode** 

### 8. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	with heatsink compound; per diode; Fig. 5	-	1.2	2	K/W
		with heatsink compound; both diodes conducting	-	0.65	1.2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	in free air	-	45	-	K/W



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## 9. Characteristics

### **Table 6. Characteristics**

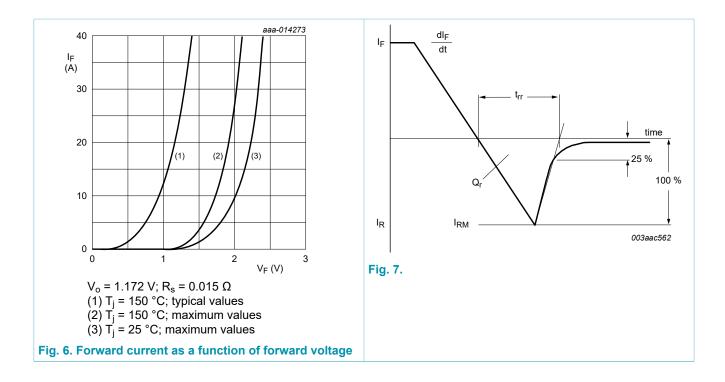
characteristics are per diode unless otherwise stated

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>F</sub>	forward voltage	I <sub>F</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 6</u>	-	1.4	2.1	V
		I <sub>F</sub> = 15 A; T <sub>j</sub> = 150 °C; <u>Fig. 6</u>	-	1.1	1.8	V
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 25 °C	-	-	10	μA
		V <sub>R</sub> = 600 V; T <sub>j</sub> = 150 °C	-	-	500	μA
Dynamic ch	naracteristics					
t <sub>rr</sub>	reverse recovery time	I <sub>F</sub> = 1 A; V <sub>R</sub> = 30 V; dI <sub>F</sub> /dt = 100 A/μs; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	25	50	ns
		$I_F$ = 15 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 25 °C; Fig. 7	-	45	-	ns
		$I_F$ = 15 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 125 °C; <u>Fig. 7</u>	-	65	-	ns
		$I_F$ = 15 A; $V_R$ = 400 V; $dI_F/dt$ = 500 A/ µs; $T_j$ = 25 °C; Fig. 7	-	34	-	ns
I <sub>RM</sub>	peak reverse recovery current	$I_F$ = 15 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 25 °C; <u>Fig. 7</u>	-	5.5	-	A
		$I_F$ = 15 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 125 °C; <u>Fig. 7</u>	-	9.7	-	A
Qr	recovered charge	$I_F$ = 15 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 25 °C; Fig. 7	-	125	-	nC
		$I_F$ = 15 A; $V_R$ = 400 V; $dI_F/dt$ = 200 A/ µs; $T_j$ = 125 °C; <u>Fig. 7</u>	-	318	-	nC

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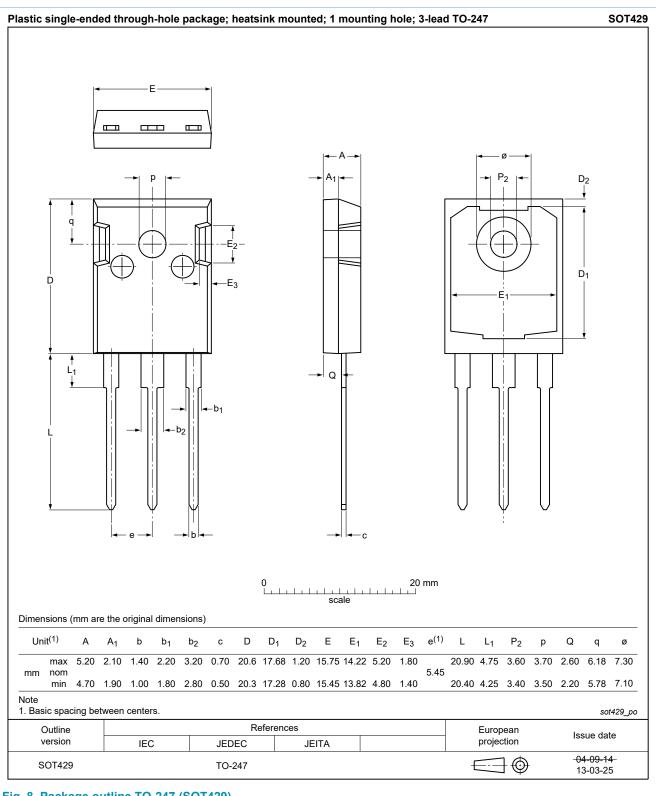
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Dual ultrafast power diode

## **10. Package outline**



### Fig. 8. Package outline TO-247 (SOT429)

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## 11. Legal information

#### **Data sheet status**

Document status [1][2]	Product status [ <u>3]</u>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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